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U.S. Department of Commerce Patent and Trademark Office

U.S. Application Serial No. 09/506,425

Atty. Docket No. AM-3751

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sara Giordani Applicants

February 17 2900

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(Use several sheets if necessary)

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Examiner Initial	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate
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ofeo	EP 0565212	Europe	10/13/93	Wong et al.	H01L	21/306	
fero	~EP 0821409	Europe	01/28/98	Coronel	H01L	21/8242	
Aus	∠EP 0822593	Europe	02/04/98	Haue et al.	H01L	21/8242	

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

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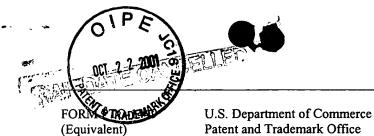
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U.S. Application Serial No. 09/506,425

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Examiner	Document	Issue				Filing Date
<u>Initial</u>	Number	<u>Date</u>	Name	<u>Class</u>	Subclass	If Appropriate

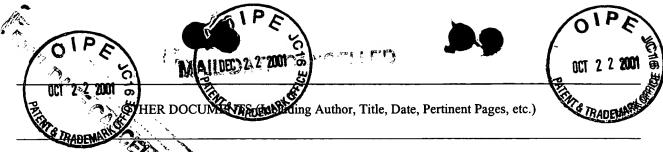
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